



Chipsmall Limited consists of a professional team with an average of over 10 year of expertise in the distribution of electronic components. Based in Hongkong, we have already established firm and mutual-benefit business relationships with customers from,Europe,America and south Asia,supplying obsolete and hard-to-find components to meet their specific needs.

With the principle of “Quality Parts,Customers Priority,Honest Operation,and Considerate Service”,our business mainly focus on the distribution of electronic components. Line cards we deal with include Microchip,ALPS,ROHM,Xilinx,Pulse,ON,Everlight and Freescale. Main products comprise IC,Modules,Potentiometer,IC Socket,Relay,Connector.Our parts cover such applications as commercial,industrial, and automotives areas.

We are looking forward to setting up business relationship with you and hope to provide you with the best service and solution. Let us make a better world for our industry!



Contact us

Tel: +86-755-8981 8866 Fax: +86-755-8427 6832

Email & Skype: info@chipsmall.com Web: www.chipsmall.com

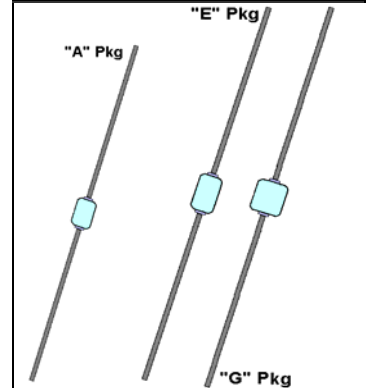
Address: A1208, Overseas Decoration Building, #122 Zhenhua RD., Futian, Shenzhen, China



DESCRIPTION

This "Ultrafast Recovery" rectifier diode series is military qualified to MIL-PRF-19500/503 and is ideal for high-reliability applications where a failure cannot be tolerated. These industry-recognized 3, 6, and 12 Amp rated rectifiers ($T_L = 70^\circ\text{C}$) in different package sizes for working peak reverse voltages from 50 to 150 volts are hermetically sealed with voidless-glass construction using an internal "Category I" metallurgical bond. These devices are also available in surface mount MELF package configurations by adding a "US" suffix (see separate data sheet for 1N6073US thru 1N6081US). Microsemi also offers numerous other rectifier products to meet higher and lower current ratings with various recovery time speed requirements including standard, fast and ultrafast device types in both through-hole and surface mount packages.

APPEARANCE



IMPORTANT: For the most current data, consult MICROSEMI's website: <http://www.microsemi.com>

FEATURES

- Popular JEDEC registered 1N6073 to 1N6081 series
- Voidless hermetically sealed glass package
- Extremely robust construction
- Triple-layer passivation
- Internal "Category I" Metallurgical bonds
- JAN, JANTX, and JANTXV available for 1N6074 and 1N6075 per MIL-PRF-19500/503
- Further options for screening in accordance with MIL-PRF-19500 for JAN, JANTX, JANTXV, or JANS by using a MQ, MX, MV or SP prefix respectively, e.g. MX6076, MV6079, SP6081, etc.
- Surface mount equivalents also available in a square end-cap MELF configuration with "US" suffix

APPLICATIONS / BENEFITS

- Ultrafast recovery rectifier series 50 to 150 V
- Military and other high-reliability applications
- Switching power supplies or other applications requiring extremely fast switching & low forward loss
- High forward surge current capability
- Low thermal resistance
- Controlled avalanche with peak reverse power capability
- Inherently radiation hard as described in Microsemi MicroNote 050

MAXIMUM RATINGS

- Junction Temperature: -65°C to $+155^\circ\text{C}$
- Storage Temperature: -65°C to $+155^\circ\text{C}$
- Peak Forward Surge Current @ 25°C : 35 Amps for 1N6073-6075, 75 Amps for 1N6076-6078, and 175 Amps for 1N6079-6081 at 8.3 ms half-sine wave
- Average Rectified Forward Current (I_o) at $T_L = +70^\circ\text{C}$ ($L = 0$ inch from body):
 1N6073 thru 1N6075: 3.0 Amps
 1N6076 thru 1N6078: 6.0 Amps
 1N6079 thru 1N6081: 12.0 Amps
 Average Rectified Forward Current (I_o) at $T_A = 55^\circ\text{C}$:
 1N6073 thru 1N6075: 0.85 Amps
 1N6076 thru 1N6078: 1.3 Amps
 1N6079 thru 1N6081: 2.0 Amps
- Thermal Resistance $L = 0$ inch ($R_{\theta JL}$): 13°C/W for 1N6073-6075, 8.5°C/W for 1N6076-6078, and 5.0°C/W for 1N6079-6081
- Solder temperature: 260°C for 10 s (maximum)

MECHANICAL AND PACKAGING

- CASE: Hermetically sealed voidless hard glass with Tungsten slugs
- TERMINATIONS: Axial-leads are Copper with Tin/Lead (Sn/Pb) finish
- MARKING: Body painted and part number, etc.
- POLARITY: Cathode indicated by band
- Tape & Reel option: Standard per EIA-296
- Weight: 1N6073 thru 1N6075: 340 mg
 1N6076 thru 1N6078: 750 mg
 1N6079 thru 1N6081: 1270 mg
- See package dimensions on last page

ELECTRICAL CHARACTERISTICS @25°C unless otherwise specified

TYPE	WORKING PEAK REVERSE VOLTAGE	MAXIMUM FORWARD VOLTAGE (PULSED)	PULSED TEST CURRENT	AVERAGE RECTIFIED CURRENT I_O @ $T_L = 70^\circ\text{C}$	AVERAGE RECTIFIED CURRENT I_O @ $T_A = 55^\circ\text{C}$	MAXIMUM REVERSE CURRENT I_R @ V_{RWM}	MAXIMUM REVERSE RECOVERY TIME*	MAXIMUM SURGE CURRENT
	V_{RWM}	V_F @ I_F	I_F	AMPS	AMPS	μA	t_{rr}	I_{FSM}
	VOLTS	VOLTS	AMPS	AMPS	AMPS	μA	ns	AMPS
1N6073	50	2.04	9.4	3.0	0.85	1.0	30	35
1N6074	100	2.04	9.4	3.0	0.85	1.0	30	35
1N6075	150	2.04	9.4	3.0	0.85	1.0	30	35
1N6076	50	1.76	18.8	6.0	1.3	5.0	30	75
1N6077	100	1.76	18.8	6.0	1.3	5.0	30	75
1N6078	150	1.76	18.8	6.0	1.3	5.0	30	75
1N6079	50	1.50	37.7	12.0	2.0	10.0	30	175
1N6080	100	1.50	37.7	12.0	2.0	10.0	30	175
1N6081	150	1.50	37.7	12.0	2.0	10.0	30	175

*NOTE: $I_F = 0.5\text{ A}$, $I_{RM} = 1.0\text{ A}$, and $I_{R(REC)} = 0.25\text{ A}$

SYMBOLS & DEFINITIONS

Symbol	Definition
V_{BR}	Minimum Breakdown Voltage: The minimum voltage the device will exhibit at a specified current.
V_{RWM}	Working Peak Reverse Voltage: The maximum peak voltage that can be applied over the operating temperature range.
V_F	Maximum Forward Voltage: The maximum forward voltage the device will exhibit at a specified current.
I_R	Maximum Leakage Current: The maximum leakage current that will flow at the specified voltage and temperature.
t_{rr}	Reverse Recovery Time: The time interval between the instant the current passes through zero when changing from the forward direction to the reverse direction and a specified recovery decay point after a peak reverse current is reached.

GRAPHS

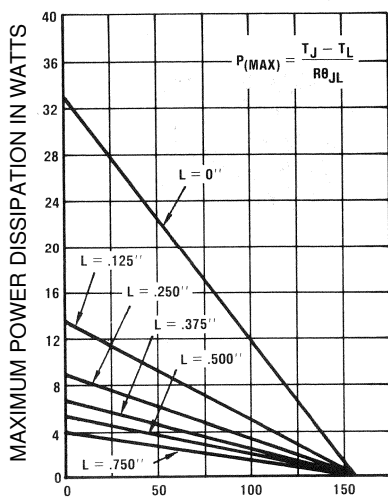


FIGURE 1

Maximum power in watts vs lead temperature for 1N6079, 1N6080 and 1N6081

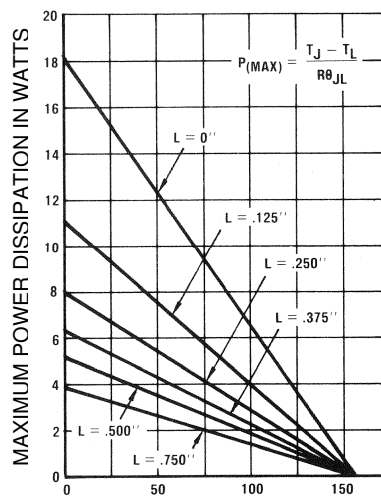


FIGURE 2

Maximum power in watts vs lead temperature for 1N6076, 1N6077 and 1N6078

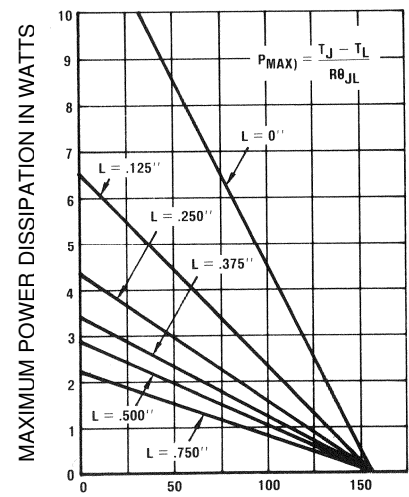


FIGURE 3

Maximum power in watts vs lead temperature for 1N6073, 1N6074 and 1N6075

Maximum lead temperature in °C (T_L) at point "L" from body (for maximum operating junction temperature with equal two-lead conditions).

Lead Length INCHES (mm)	R _{θJL} °C/W
0.000	5.0
0.125 (3.17)	11.5
0.250 (6.35)	17.5
0.375 (9.53)	23.5
0.500 (12.70)	29.0
0.750 (19.05)	40.0

1N6079, 1N6080 and 1N6081

Lead Length INCHES (mm)	R _{θJL} °C/W
0.000	8.5
0.125 (3.17)	14.0
0.250 (6.35)	19.5
0.375 (9.53)	25.0
0.500 (12.70)	30.0
0.750 (19.05)	40.0

1N6076, 1N6077 and 1N6078

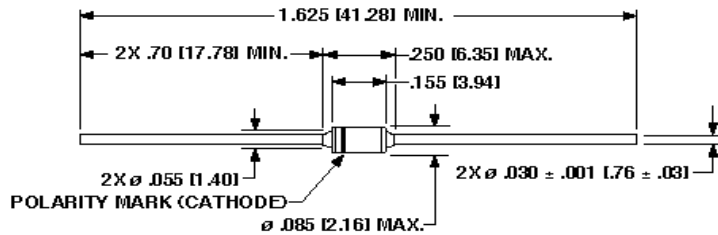
Lead Length INCHES (mm)	R _{θJL} °C/W
0.000	13
0.125 (3.17)	24
0.250 (6.35)	35
0.375 (9.53)	46
0.500 (12.70)	54
0.750 (19.05)	70

1N6073, 1N6074 and 1N6075

NOTES:

1. Dimensions are in inches
2. Metric equivalents (to the nearest .01mm) are given for general information only and are based upon 1 inch = 25.4 mm.

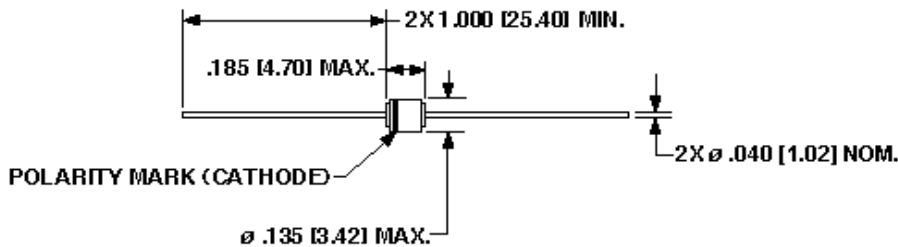
PACKAGE DIMENSIONS



NOTE: DIMENSIONS IN INCHES [mm]

PACKAGE A (1N6073-75)

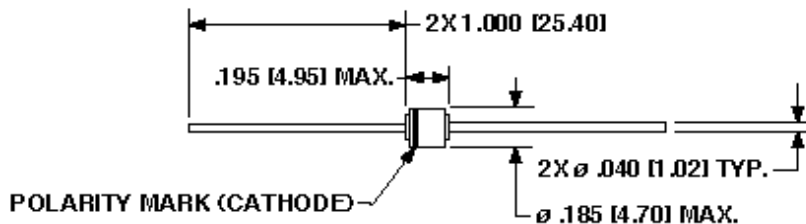
NOTE: Lead diameter tolerance = +0.003/-0.004 inches



NOTE: DIMENSIONS IN INCHES [MM]

PACKAGE E (1N6076-78)

NOTE: Lead diameter tolerance = +0.002/-0.003 inches



NOTE: DIMENSIONS IN INCHES [MM]

PACKAGE G (1N6079-81)

NOTE: Lead diameter tolerance = +0.002/-0.003 inches